





	°C					
	°C					
	°C					
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	°C					
	°C					
	°C					



FIG.1: Power dissipation vs. on-state current
(per thyristor or diode)
 $P_T(AV)/P_F(AV)(W)$

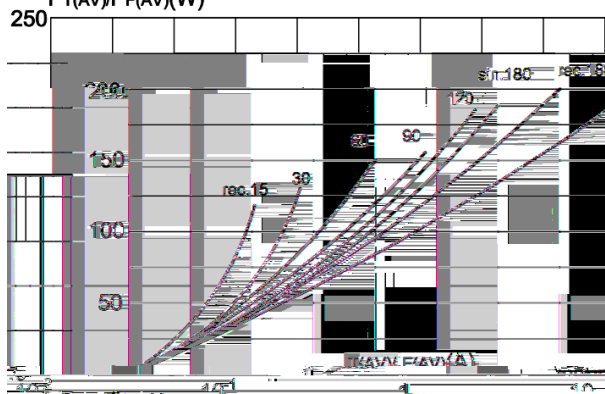


FIG.2: Maximum transient thermal impedance
junction to case(per thyristor or diode)
 $R_{th(j-c)}(^{\circ}C/W)$

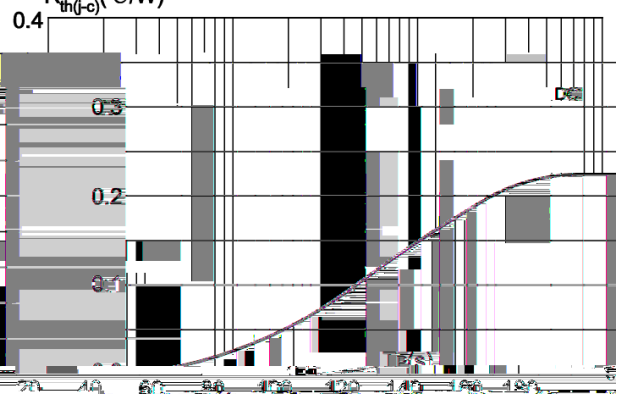


FIG.3: Forward characteristics
(per thyristor or diode)
 $I_F(A)/I_T(A)$

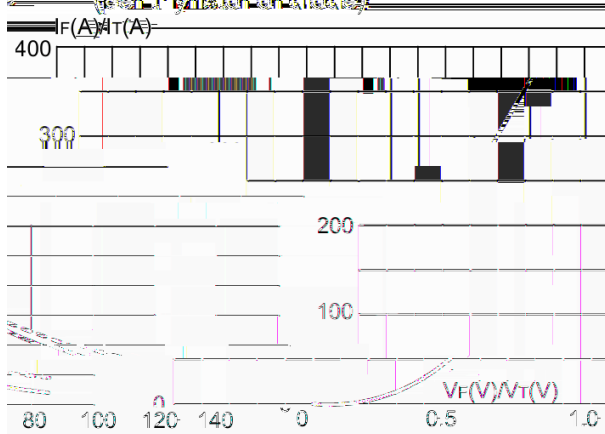


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature
 $I_{GT, IH, IL}(T)/I_{GT, IH, IL}(T_{J=25^{\circ}C})$

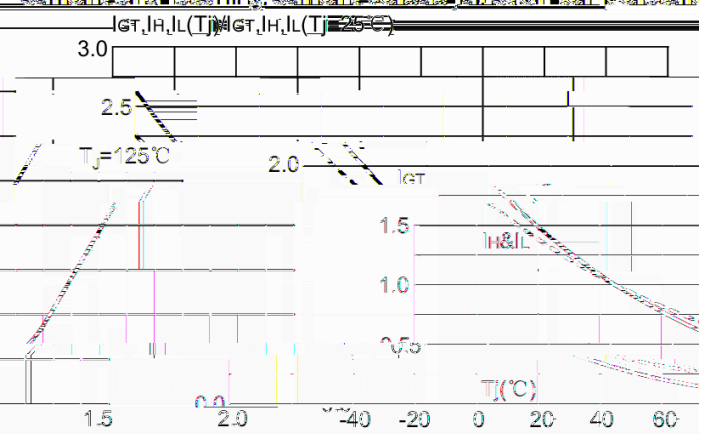


FIG.5: Gate trigger characteristics
 $V_G(V)$



FIG.6: Forward current vs. case temperature
 $I_F(AV)(A)$ (per thyristor or diode)

